

ABSTRACT OF THE DISCLOSURE

A semiconductor laser device capable of improving heat dissipativity, simplifying the fabrication process and improving the fabrication yield is obtained. This
5 semiconductor laser device comprises a semiconductor layer formed on an emission layer while constituting a convex ridge portion, a current blocking layer consisting of a semiconductor formed to cover at least the side surfaces of the ridge portion, a first metal electrode formed to be
10 in contact with the upper surface of the ridge portion and convex support portions arranged on both sides of the ridge portion at a prescribed interval from the ridge portion.